Unit: mm

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

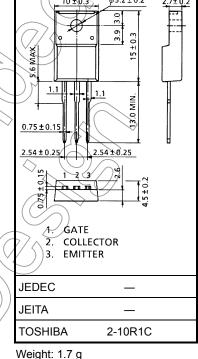
GT15J321

High Power Switching Applications Fast Switching Applications

- Fourth-generation IGBT
- Fast switching (FS
- Enhancement mode type
- High speed: $t_f = 0.03 \mu s$ (typ.)
- Low saturation Voltage: $V_{CE (sat)} = 1.90 \text{ V (typ.)}$
- FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

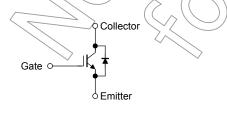
| Characteristics | | Symbol | Rating | Unit | |
|---|------|------------------|---------|---|--|
| Collector-emitter voltage | | V _{CES} | 600 | V | |
| Gate-emitter voltage | | V _{GES} | +20 | V | |
| Collector current | DC | IC | 15 | A | |
| | 1 ms | I _{CP} | 30 | | |
| Emitter-collector forward current | DC | l _F | 15 | A | |
| | 1 ms | IFM | 30 | | |
| Collector power dissipation (Tc = 25°C) | | PC | 30 | w | |
| Junction temperature | | (Jj.)) | 150 | Źζ¢ | |
| Storage temperature range | | Tstg | -55~150 | \rightarrow \cdot | |



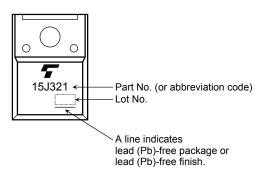
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit



Marking

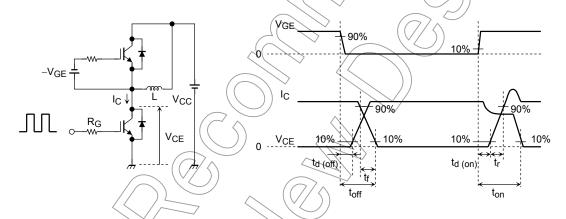


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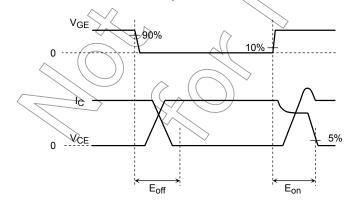
Electrical Characteristics (Ta = 25°C)

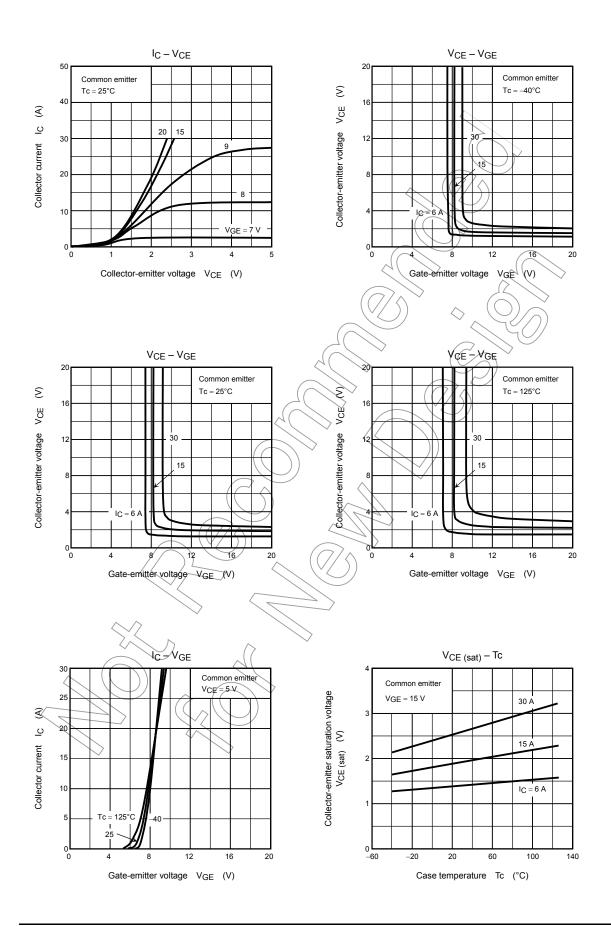
| Chara | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|----------------------|--------------------|-----------------------|---|--------------|-------|------|------|
| Gate leakage cur | rent | I _{GES} | $V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$ | _ | _ | ±500 | nA |
| Collector cut-off of | current | I _{CES} | V _{CE} = 600 V, V _{GE} = 0 | _ | _ | 1.0 | mA |
| Gate-emitter cut- | off voltage | V _{GE} (OFF) | I _C = 1.5 mA, V _{CE} = 5 V | 3.5 | _ | 6.5 | V |
| Collector-emitter | saturation voltage | V _{CE} (sat) | I _C = 15 A, V _{GE} = 15 V | | 1.90 | 2.45 | V |
| Input capacitance |) | C _{ies} | $V_{CE} = 20 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$ | (F | 2300 | _ | pF |
| Switching time Fall | Rise time | t _r | Inductive Load | <u> </u> | 0.04 | _ | μs |
| | Turn-on time | ton | V _{CC} = 300 V, I _C = 15 A |) | 0.17 | _ | |
| | Fall time | t _f | $V_{GG} = 15 \text{ V}, R_G = 43 \Omega$ | · — | 0.03 | 0.15 | |
| | Turn-off time | t _{off} | (Note 1) | _ | 0.34 | | |
| Peak forward volt | age | V _F | I _F = 15 A, V _{GE} = 0 | _ | 4 | 2.0 | V |
| Reverse recovery | time | t _{rr} | $I_F = 15 \text{ A}, \text{ di/dt} = -100 \text{ A/µs}$ | | \$ 7/ | 200 | ns |
| Thermal resistance | ce (IGBT) | R _{th (j-c)} | (4/3) | -((| | 4.16 | °C/W |
| Thermal resistance | ce (Diode) | R _{th (j-c)} | | 4 | 4 | 4.63 | °C/W |

Note 1: Switching time measurement circuit and input/output waveforms

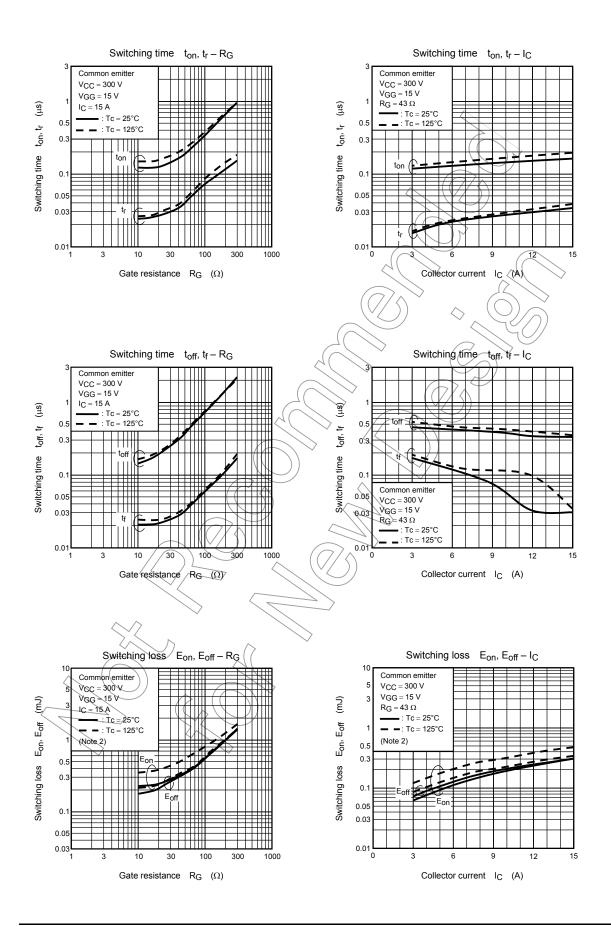


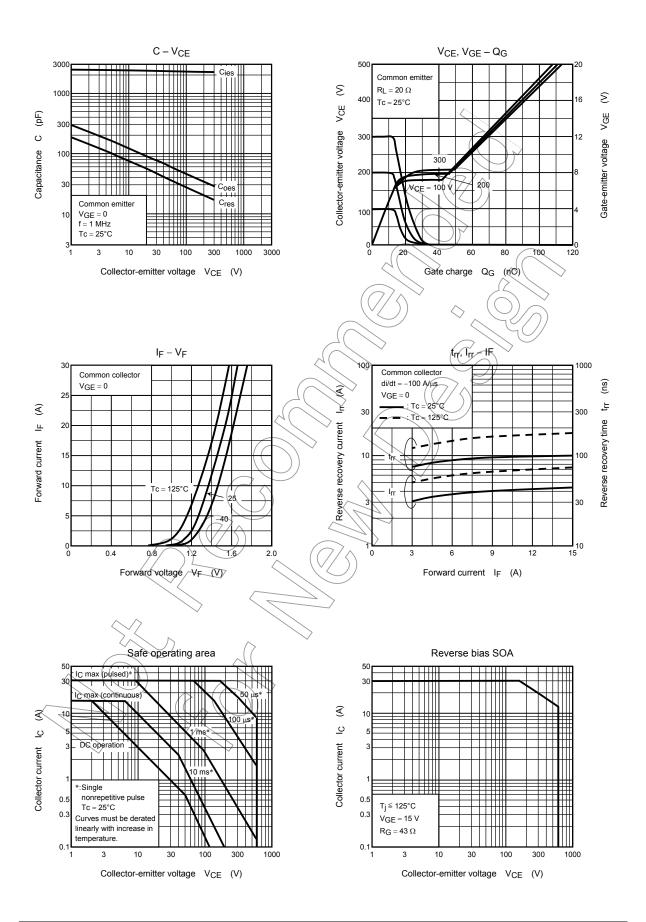
Note 2: Switching loss measurement waveforms



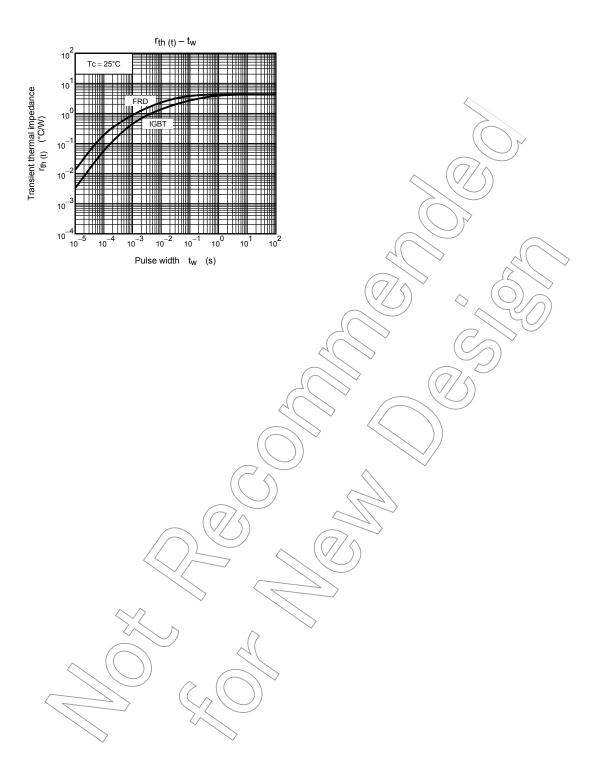


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